

Equivalent Circuit Description of Non-compensated n-p Codoped T_iO_2 as Intermediate Band Solar Cells

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The novel concept of non-compensated n-p codoping has made it possible to create tunable intermediate bands in the intrinsic band gap of T_iO_2 , making the codoped T_iO_2 a promising material for developing intermediate band solar cells (IBSCs). Here we investigate the quantum efficiency of such IBSCs within two scenarios - with and without current extracted from the extended intermediate band. Using the ideal equivalent circuit model, we find that the maximum efficiency of 57% in the first scenario and 53% in the second are both much higher than the Shockley-Queisser limit from single gap solar cells. We also obtain various key quantities of the circuits, a useful step in realistic development of T_iO_2 based solar cells invoking device integration. These equivalent circuit results are also compared with the efficiencies obtained directly from consideration of electron transition between the energy bands, and both approaches reveal the intriguing existence of double peaks in the maximum quantum efficiency as a function of the relative location of IBs.

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I. INTRODUCTION

Recently inspired by the highly theoretical efficiency of Intermediate Band Solar Cells (IBSCs), many have put much effort into the investigation of the double-gap and even multiple-gap devices, including both the new materials research and the theoretical calculations. In the aspect of searching for new satisfactory materials, the novel concept of non-compensated n-p codoping has made it possible to create tunable intermediate bands in the intrinsic band gap of T_iO_2 [1], making the codoped T_iO_2 a promising material for developing intermediate band solar cells (IBSCs). Inspiringly, in the other aspect, the theoretical calculation has shown that the maximum efficiency has significantly increased by introducing an impurity energy level in the semiconductor band gap that absorbs additional lower energy photons [2–5].

In the meanwhile, above the direct description of the transitions between energy bands, another approach of equivalent circuit description has been much deeply studied in many aspects. Considering the existence of the small trivial effects [6–9], such as overlap between absorption coefficients, the dual presence of impact ionization and Auger recombination phenomena, A. Luque *et al.* have proposed the general equivalent circuit approach to IBSCs [10], in addition to which, the equivalent circuit models of multi-level devices have been discussed in Ref. [11]. Respectively, the equivalent circuit approach to organic solar cells has been studied in Ref. [12, 13]. Both direct and equivalent circuit description show that the maximum efficiency of 63% of IBSCs is much larger than

that of single gap devices (41%).

Trying the difference of extracting current from IBs, in this paper, we will discuss the equivalent circuit description of general single-gap and double-gap solar cells in section II, including the two scenarios – with and without current extracted from IBs. Then we turn to the equivalent circuit investigation of T_iO_2 based IBSCs in section III. We will realize the improvement caused by the extracted current, and find the intriguing existence of double peaks in the maximum quantum efficiency as a function of the relative location of IBs in the two sections.

II. THE MAXIMUM EFFICIENCY OF A GENERAL IBSC

Ignoring the small trivial effects described in section I, we can obtain the ideal equivalent circuits of single-gap and double-gap solar cells, described in Fig. 1(b) and Fig. 1(c) respectively, where the current sources represent the generation of photo-current after absorbing photons between X and Y (X and Y represent CB, IB and VB respectively), and the diodes represent the recombination.

According to the black-body radiation assumption, we have:

$$J_{L,CV} = F(E_C, \infty, T_S) - F(E_C, \infty, T_C), \quad (1)$$

$$F(E_A, E_B, T) = \frac{2\pi}{h^3 c^2} \int_{E_B}^{E_A} \frac{\varepsilon^2}{\exp\left(\frac{\varepsilon - \mu}{kT}\right) - 1} d\varepsilon, \quad (2)$$

with $\mu = 0$

$$J_{XY} = J_{0,XY} \left(\exp \frac{eV_{XY}}{kT_C} - 1 \right), \quad (3)$$

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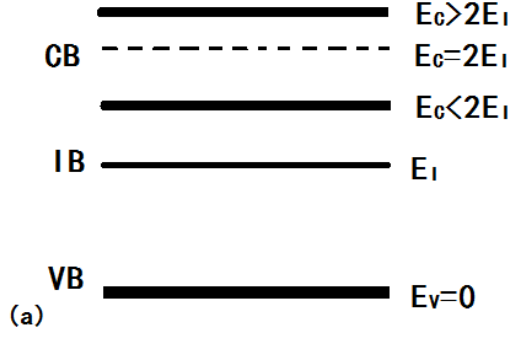
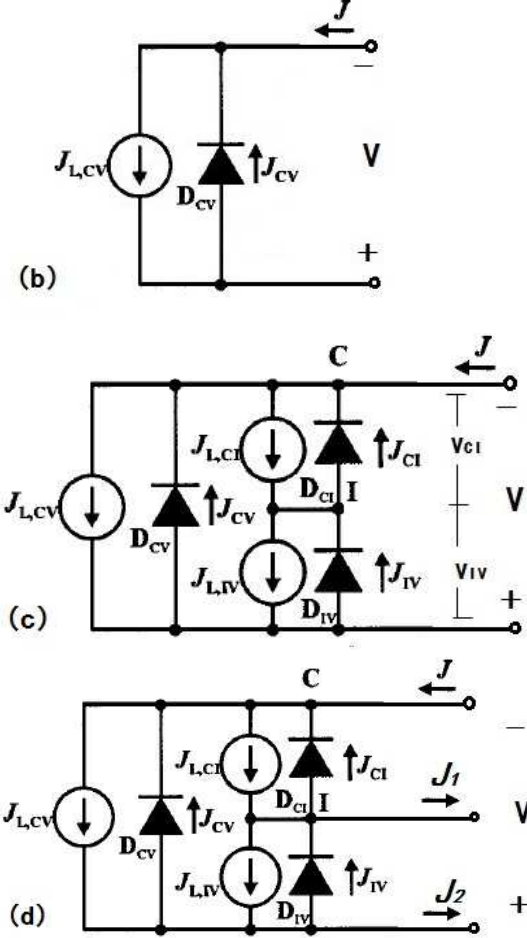


FIG. 1: (a): The energy level of XB is E_X , with X representing I , C and V . (b), (c) and (d) are the equivalent circuits of single-gap solar cells, double-gap solar cells without and with current from IBs, respectively.

$$J_{0,XY} = \frac{2\pi}{h^3 c^2} \int_{E_{XY}}^{\infty} \varepsilon^2 \exp\left(\frac{-\varepsilon}{kT}\right) d\varepsilon. \quad (4)$$

For single gap solar cells, the efficiency can be written as

$$\eta = J \cdot V / \left(\frac{\pi^2 k^4}{60 c^2 h^3} T_S^4 \right).$$

With the condition $0 < V < E_C/e$, we obtained maximum efficiency for each value of E_C and then in Fig. 2, the maximum efficiency as a function of the location of CBs of single gap solar cells, we find the value of the peak is about 40.8% at about $E_C = 1.1\text{eV}$, which highly agrees with that obtained by the direct description of electron transitions in Ref. [5].

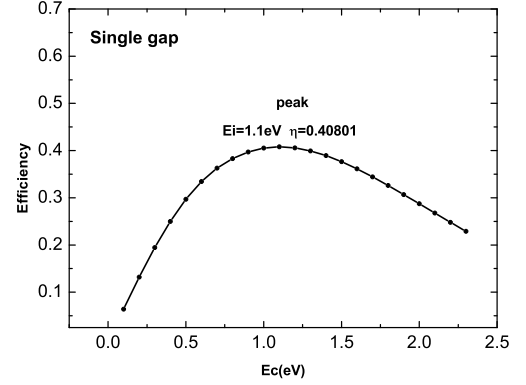


FIG. 2: The maximum efficiency of single-gap solar cells as a function of the location of IBs.

If an impurity band is introduced between VB and CB, the situation becomes complex. More specifically, when $E_I < E_C < 2E_I$, the electron transitions between VBs and IBs are produced by the photons with energy $\varepsilon \in (E_I, E_C)$, and that between IBs and CBs are provided by the photons with energy $\varepsilon \in (E_C - E_I, E_I)$.

$$J_{L,CI} = F(E_C - E_I, E_I, T_S) - F(E_C - E_I, E_I, T_C) \quad (5)$$

$$J_{L,IV} = F(E_I, E_C, T_S) - F(E_I, E_C, T_C) \quad (6)$$

On the other hand, when $E_C > 2E_I$, the electron transitions between VBs and IBs are produced by the photons with energy $\varepsilon \in (E_I, E_C - E_I)$, and that between IBs and CBs are provided by the photons with energy $\varepsilon \in (E_C - E_I, E_C)$.

$$J_{L,CI} = F(E_C - E_I, E_C, T_S) - F(E_C - E_I, E_C, T_C) \quad (7)$$

$$J_{L,IV} = F(E_I, E_C - E_I, T_S) - F(E_I, E_C - E_I, T_C) \quad (8)$$

The total current is $J = J_{L,CV} - J_{CV} + J_{L,CI} - J_{CI}$, total voltage is $V = V_{IV} + V_{CI}$. For an arbitrary set of

E_I and E_C , we choose V_{IV} and V_{CI} from $V_{IV} < E_I/e$ and $V_{CI} < (E_C - E_I)/e$ to find the maximum efficiency. Then the maximum efficiency as a function of the location of IBs is plotted in Fig. 3(a), in which we can find two peaks at about $E_I = 0.7\text{eV}$ and $E_I = 1.2\text{eV}$ respectively with the efficiency value about $\eta = 63.5\%$, which is much larger than that of single gap solar cells.

It should be noticed that with no current flowing from IBs, the amount of electrons in IBs is invariable. This is reflected in the equivalent circuit model (Fig. 1(c)), which has a restriction of current at the point I , written as $J_{L,CV} - J_{CV} = J_{L,IV} - J_{IV}$. This restriction leads to a result that there will be no solution to the circuit to some value of E_C and E_I , for the restriction is too strong. This is also the reason why the black curve in Fig. 3(a) is of some distortion. This distortion will disappear when we consider the partial absorption which will be discussed in the following section.

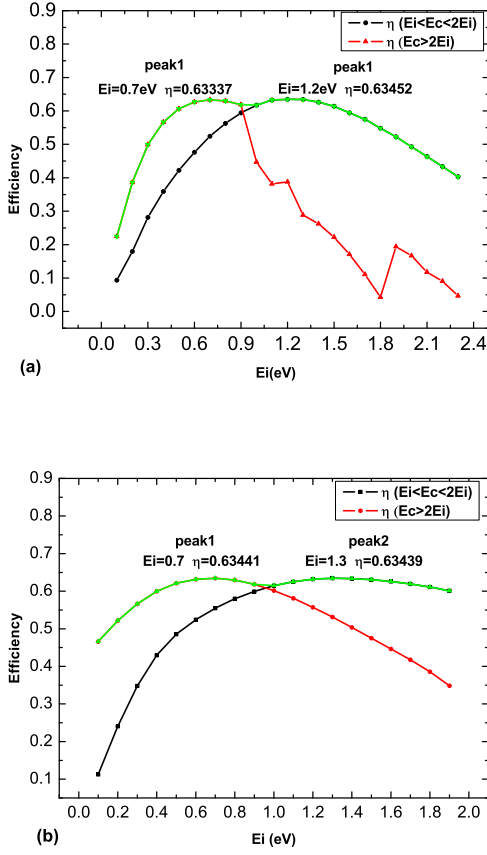


FIG. 3: (a) and (b) represent the maximum efficiency of IB-SCs without and with current extracted from IBs as a function of the location of IBs, respectively.

Now if we extract current from IBs (Fig. 1(d)), the current restriction at point I will disappear, and as a result there are solutions to all the E_C and E_I with $E_C > E_I$.

In Fig. 3(b), with the efficiency

$$\eta = (J_1 \cdot V_{CI} + J_2 \cdot (V_{IV} + V_{CI})) / \left(\frac{\pi^2 k^4}{60 c^2 \hbar^3} T_S^4 \right),$$

we find the corresponding distortion disappears, and the maximum efficient has not changed significantly at about 63.5%. But we will see the change of extracting current from IBs will lead to much difference if we fixed the value of E_C (section III).

III. DESCRIPTION OF TiO_2 BASED SOLAR CELLS

To the TiO_2 based solar cells, the energy level of CBs is fixed to $E_C = 3.2\text{eV}$. The maximum efficiency as a function of E_I has been plotted in Fig. 4, (a) and (b) represent the two scenarios – without and with current extracted from IB respectively. Clearly, the maximum efficiency of 56.7% in the second scenario is larger than that of 52.6% in the first scenario.

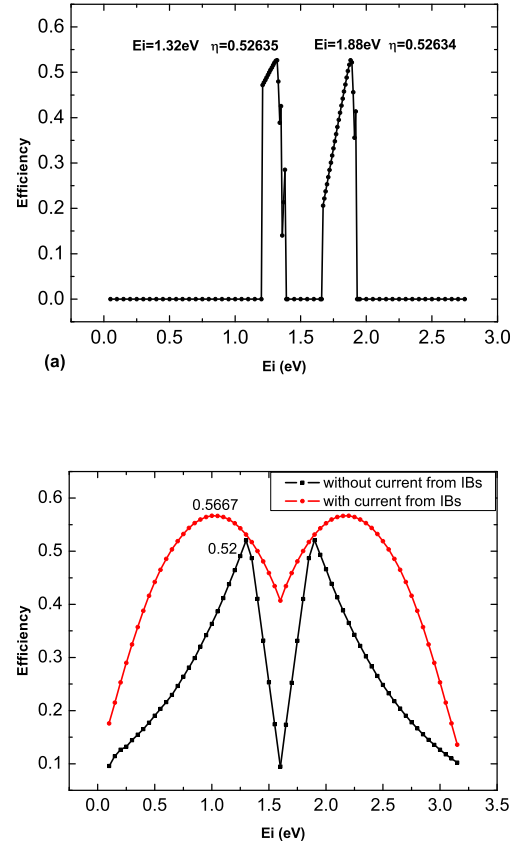


FIG. 4: (a) and (b) represent the maximum efficiency of TiO_2 based IBSCs without and with current extracted from IBs as a function of the location of IBs respectively, with the consideration of partial absorption.

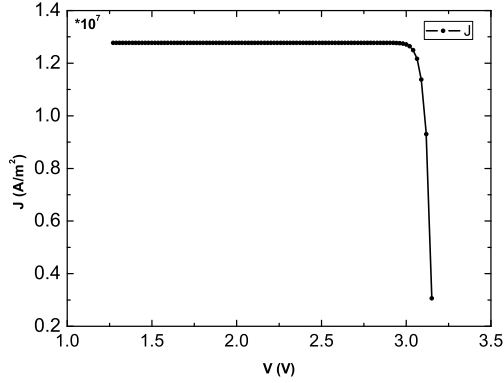


FIG. 5: The volt-ampere characteristic curve of TiO_2 based solar cell with $E_I = 3.2\text{eV}$ (no current extracted from IBs).

In the first scenario there are no solutions to some values of E_I , which is impossible for a real physical process. The factor which leads to the "no solution" result is the assumption of complete absorption between any two bands. So we should consider the situation of partial absorption, which means that the currents of $J_{L,IV}$ and $J_{L,CI}$ should be smaller than the values given in the equations (5-8). In this consideration, the quantum efficiency of the TiO_2 based solar cells is plotted in Fig. 4(b).

To have a further insight of the equivalent circuit, in Fig. 5 we obtained the output characteristics of the circuit (Fig. 1(d)) with E_C and E_I fixed to 3.2eV and 1.3eV . With the increase of the output voltage, the output current keeps constant until V reaches to about 3V . This is similar to a current source in parallel with a diode, whose turn-on voltage is about 3V .

IV. CONCLUSIONS

First, having got the ideal equivalent circuit model for IBSC, we obtained the the maximum efficiency of a general IBSC as a function of the relative location of IBs, and found the maximum efficiency of 63% is much larger than that of the single gap solar cells of 41% . More interestingly, there are two peaks in the two sides of $E_I = E_C/2$, and we should consider the two sides desperately for the physical procedure of them are different. But under the assumption of completely absorbing the external illumination, which is set for getting the maximum efficiency, there will be no solution to some values of E_I and E_C because of the charge conservation in IBs. So we considered the partial absorption situation, which successfully solve this problem. However, the consideration of partial absorption will inevitably reduce its efficiency. Based on this, we put forward a new idea of extracting current from IBs. This idea shows a significant improvement for the TiO_2 based solar cells, and the maximum efficiency has increased from 52% to 57% . For TiO_2 , a promising material to develop the IBSCs, we got the key qualities of the equivalent circuits, from which we can build a simplified circuit for more complicated structures.

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